

### A1015LT1 TRANSISTOR (PNP)

\* “G” Lead(Pb)-Free

#### FEATURES

Power dissipation

$P_{CM}$ : 0.2 W ( $T_{amb}=25^\circ\text{C}$ )

Collector current

$I_{CM}$ : -0.15 A

Collector-base voltage

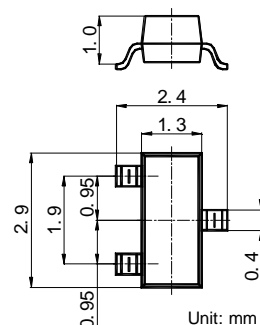
$V_{(BR)CBO}$ : -50 V

Operating and storage junction temperature range

$T_J, T_{stg}$ : -55 to +150

#### SOT-23

1. BASE
2. EMITTER
3. COLLECTOR



#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1\text{mA}, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -50\text{V}, I_E = 0$			-0.1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CE} = -50\text{V}, I_B = 0$			-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	$\mu\text{A}$
DC current gain	$H_{FE(1)}$	$V_{CE} = -6\text{V}, I_C = -2\text{mA}$	130		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-1.1	V
Transition frequency	$f_T$	$V_{CE} = -10\text{V}, I_C = -1\text{mA}$ $f = 30\text{MHz}$	80			MHz

#### CLASSIFICATION OF $H_{FE(1)}$

Rank	L	H
Range	130-200	200-400
MARKING	BA	

